





EH35 00

Series -RoHS Compliant (Pb-free) 5.0V 4 Pad 3.2mm x 5mm Ceramic SMD HCMOS/TTL High Frequency Oscillator

Frequency Tolerance/Stability ±100ppm Maximum

Operating Temperature Range - 0°C to +70°C

TS -12.000M

Nominal Frequency 12.000MHz

Pin 1 Connection
 Tri-State (Disabled Output: High Impedance)

Duty Cycle 50 ±10(%)

Frequency Tolerance/Stability 2 O Si Aging at 25°C 2 Operating Temperature Range 2 0°	12.000MHz ±100ppm Maximum (Inclusive of all conditions: Calibration Tolerance at 25°C, Frequency Stability over the Operating Temperature Range, Supply Voltage Change, Output Load Change, 1st Year Aging at 25°C, Shock, and Vibration) ±5ppm/year Maximum 0°C to +70°C 5.0Vdc ±10% 50mA Maximum (No Load)	
Aging at 25°C ±5 Operating Temperature Range 0°	Operating Temperature Range, Supply Voltage Change, Output Load Change, 1st Year Aging at 25°C, Shock, and Vibration) ±5ppm/year Maximum 0°C to +70°C 5.0Vdc ±10%	
Operating Temperature Range 0°	0°C to +70°C 5.0Vdc ±10%	
	5.0Vdc ±10%	
Supply Voltage 5.		
	FOm A Mayimum (No. Load)	
Input Current 50	Softia Maximum (No Edad)	
Output Voltage Logic High (Voh) 2.	2.4Vdc Minimum with TTL Load, Vdd-0.4Vdc Minimum with HCMOS Load (IOH = -16mA)	
Output Voltage Logic Low (Vol) 0.	0.4Vdc Maximum with TTL Load, 0.5Vdc Maximum with HCMOS Load (IOL = +16mA)	
	6nSec Maximum (Measured at 0.8Vdc to 2.0Vdc with TTL Load or at 20% to 80% of waveform with HCMOS Load)	
Duty Cycle 50	50 ±10(%) (Measured at 1.4Vdc with TTL Load or at 50% of waveform with HCMOS Load)	
Load Drive Capability 10	10TTL Load or 50pF HCMOS Load Maximum	
Output Logic Type C	CMOS	
Pin 1 Connection Tr	Tri-State (Disabled Output: High Impedance)	
	+2.2Vdc Minimum to enable output, +0.8Vdc Maximum to disable output (High Impedance), No Connec enable output.	
Absolute Clock Jitter ±2	±250pSec Maximum, ±100pSec Typical	
One Sigma Clock Period Jitter ±5	±50pSec Maximum, ±30pSec Typical	
Start Up Time 10	10mSec Maximum	
Storage Temperature Range -5	-55°C to +125°C	

ENVIRONMENTAL & MECHANICAL SPECIFICATIONS		
Fine Leak Test	MIL-STD-883, Method 1014, Condition A	
Gross Leak Test	MIL-STD-883, Method 1014, Condition C	
Mechanical Shock	MIL-STD-202, Method 213, Condition C	
Resistance to Soldering Heat	MIL-STD-202, Method 210	
Resistance to Solvents	MIL-STD-202, Method 215	
Solderability	MIL-STD-883, Method 2003	
Temperature Cycling	MIL-STD-883, MEthod 1010	
Vibration	MIL-STD-883, Method 2007, Condition A	



MECHANICAL DIMENSIONS (all dimensions in millimeters)



PIN CONNECTION	
1	Tri-State
2	Ground/Case Ground
3	Output
4	Supply Voltage

LINE	MARKING
1	E12.000 E=Ecliptek Designator

Suggested Solder Pad Layout

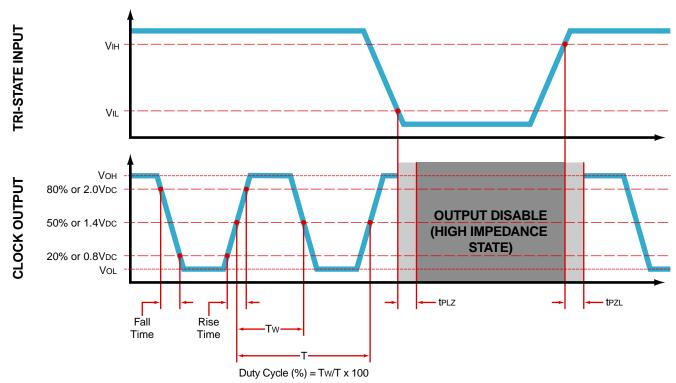
All Dimensions in Millimeters



All Tolerances are ±0.1



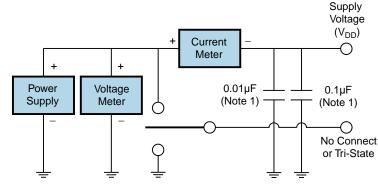
OUTPUT WAVEFORM & TIMING DIAGRAM

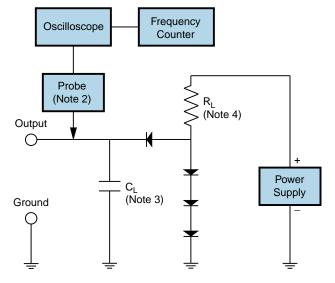


Test Circuit for TTL Output

Output Load Drive Capability	R _L Value (Ohms)	C _L Value (pF)
10TTL	390	15
5TTL	780	15
2TTL	1100	6
10LSTTL	2000	15
1TTL	2200	3

Table 1: R_L Resistance Value and C_L Capacitance Value Vs. Output Load Drive Capability





Note 1: An external $0.1\mu F$ low frequency tantalum bypass capacitor in parallel with a $0.01\mu F$ high frequency ceramic bypass capacitor close to the package ground and V_{DD} pin is required.

Note 2: A low capacitance (<12pF), 10X attenuation factor, high impedance (>10Mohms), and high bandwidth (>300MHz) passive probe is recommended.

Note 3: Capacitance value C_{L} includes sum of all probe and fixture capacitance.

Note 4: Resistance value R_L is shown in Table 1. See applicable specification sheet for 'Load Drive Capability'.

Note 5: All diodes are MMBD7000, MMBD914, or equivalent.



Test Circuit for CMOS Output



Note 1: An external $0.1\mu\text{F}$ low frequency tantalum bypass capacitor in parallel with a $0.01\mu\text{F}$ high frequency ceramic bypass capacitor close to the package ground and V_{DD} pin is required.

Note 2: A low capacitance (<12pF), 10X attenuation factor, high impedance (>10Mohms), and high bandwidth (>300MHz) passive probe is recommended.

Note 3: Capacitance value \dot{C}_L includes sum of all probe and fixture capacitance.



Recommended Solder Reflow Methods



High Temperature Infrared/Convection

T _S MAX to T _L (Ramp-up Rate)	3°C/second Maximum
Preheat	
- Temperature Minimum (T _s MIN)	150°C
- Temperature Typical (T _s TYP)	175°C
- Temperature Maximum (T _s MAX)	200°C
- Time (t _s MIN)	60 - 180 Seconds
Ramp-up Rate (T _L to T _P)	3°C/second Maximum
Time Maintained Above:	
- Temperature (T∟)	217°C
- Time (t∟)	60 - 150 Seconds
Peak Temperature (T _P)	260°C Maximum for 10 Seconds Maximum
Target Peak Temperature (T _P Target)	250°C +0/-5°C
Time within 5°C of actual peak (tp)	20 - 40 seconds
Ramp-down Rate	6°C/second Maximum
Time 25°C to Peak Temperature (t)	8 minutes Maximum
Moisture Sensitivity Level	Level 1



Recommended Solder Reflow Methods



Low Temperature Infrared/Convection 240°C

T _s MAX to T _L (Ramp-up Rate)	5°C/second Maximum
Preheat	
- Temperature Minimum (T _s MIN)	N/A
- Temperature Typical (T _s TYP)	150°C
- Temperature Maximum (T _s MAX)	N/A
- Time (t _s MIN)	60 - 120 Seconds
Ramp-up Rate (T _L to T _P)	5°C/second Maximum
Time Maintained Above:	
- Temperature (T _L)	150°C
- Time (t∟)	200 Seconds Maximum
Peak Temperature (T _P)	240°C Maximum
Target Peak Temperature (T _P Target)	240°C Maximum 1 Time / 230°C Maximum 2 Times
Time within 5°C of actual peak (tp)	10 seconds Maximum 2 Times / 80 seconds Maximum 1 Time
Ramp-down Rate	5°C/second Maximum
Time 25°C to Peak Temperature (t)	N/A
Moisture Sensitivity Level	Level 1

Low Temperature Manual Soldering

185°C Maximum for 10 seconds Maximum, 2 times Maximum.

High Temperature Manual Soldering

260°C Maximum for 5 seconds Maximum, 2 times Maximum.